

IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please ADD the following paragraph beginning at line 8 on page 8 of the specification to copy claims 3-4, as amended, into the specification:

A dynamic burn-in apparatus for a semiconductor device, wherein a signal output from a signal generator is provided to a semiconductor device to be tested in the burn-in tank, comprising: a converter that is added at the output of the signal generator and located outside of the semiconductor device, wherein the frequency of the signal output from the signal generator is increased by the converter and the signal output from the converter is provided to the semiconductor device. In one embodiment, the converter comprises a synchronous oscillator and a waveform shaping circuit, wherein the synchronous oscillator is synchronized with a clock output from the signal generator and generates a clock having higher frequency than that of the clock output from the signal generator, and the waveform shaping circuit shapes a control signal (such as, for example, the write enable control signal WE1), a data signal (such as, for example, data signal DIN1) and an address signal output from the signal generator into the control signal, the data signal and the address signal that have the width corresponding to the clock output from the synchronous oscillator, wherein the clock output from the synchronous oscillator and the control signal, the data signal and the address signal output from the waveform shaping circuit are provided to the semiconductor device.

Please AMEND the paragraph on lines 22-23 of page 3 of the specification as follows:

Figs. 1a and 1b ~~Fig. 1a and 1b~~ show a schematic diagram according to the present invention.

Please AMEND the paragraph on page 4, lines 26-30 as follows:

The frequency f of the signal output from the signal generator 1 is multiplied by N times ($N = 1, 2, \dots$) by the ~~generator 3~~generator 1. The burn-in signal output from the ~~generator 3~~generator 1 is input to the semiconductor device when the dynamic burn-in is operated.

Please AMEND the paragraph on page 5, lines 4-14 as follows:

Fig. 2 shows a schematic diagram of a burn-in apparatus according to the embodiment

of the present invention. The burn-in apparatus has the converter 3 at the output from the signal generator 1. The converter 3 raises the frequency of the ~~signal~~-signals output from the signal generator 1 and provides a signal having a higher frequency to general-purpose semiconductor devices in the burn-in tank 2. Thus, the burn-in is accelerated. In addition, the present invention cannot only be applied to a general-purpose semiconductor device but can be applied to other kinds of semiconductor devices.